



Features

- High Voltage Optocoupler
- Integrated Low Voltage LED Drivers with 10kV Photo Detector Diode
- Black Casing, Light Tight Packaging
- Custom Versions Available

Specifications1

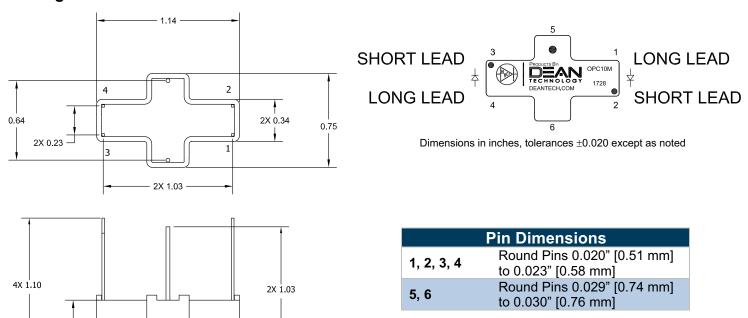
Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	Ι _R μΑ	I _{FSM} A	С _Ј pF	CTR %	t _{on} μs	t _{OFF} μs	Insulation Voltage V	l _{LED} mA	V _{FLED} V	V _{RLED} V
OPC10M	10000	80	12	25	10	3	0.48	2	2	12000	100	1.25	5

Temperature °C						
Operating Temperature	-40 to 85					
Storage Temperature	-55 to 100					
Maximum Junction Temperature	100					

125°C ambient temperature unless stated otherwise.

Drawings

0.45



VERSION: 3.0 EFFECTIVE: 27 DECEMBER 2021 PAGE: 1 OF 3





Test Circuit

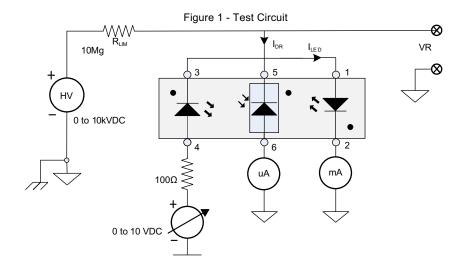
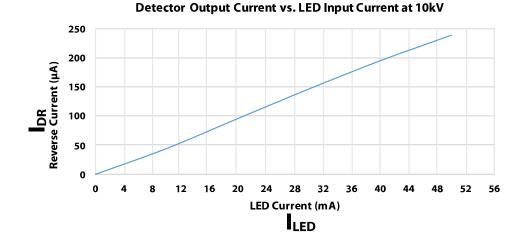
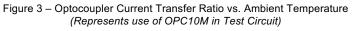
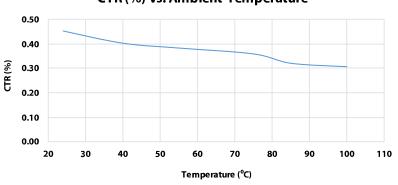


Figure 2 - Photo Detector Diode Current vs. LED Current







CTR (%) vs. Ambient Temperature

HVP High Voltage Products GmbH | +49 89 864 6677-0 | info@hvproducts.de | www.hvproducts.de

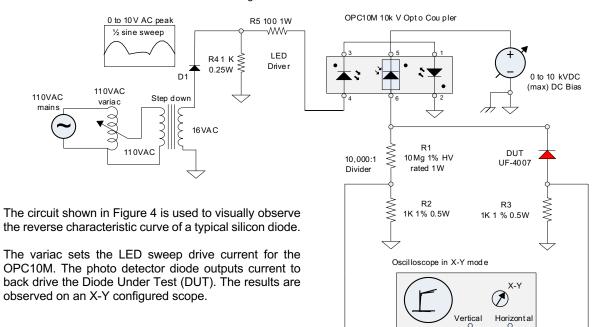
VERSION: 3.0 EFFECTIVE: 27 DECEMBER 2021 PAGE: 2 OF 3





Sample Application Circuit

Figure 4 – Visual Diode Tester



Specification Definitions

	Specifications	Conditions
V _{RRM}	Maximum Repetitive Reverse Voltage	-
IFAVM	Maximum Average Forward Current	At $T_A = 55^{\circ}C$
VF	Maximum Forward Voltage Drop	At I _F = 100mA
I _R ²	Maximum Leakage Current	At V _{DR} = V _{RRM} , I _{LED} = 0mA
I _{FSM}	Maximum Surge Current	At 60Hz, Single Half Sine
CJ	Typical Junction Capacitance	At V_R = 0VDC, f = 1MHz
CTR	Current Transfer Ratio	I _{LED} = 50mA for 1 sec
ton	Turn-on Time	-
toff	Turn-off Time	-
Insulation Voltage	-	LED Drivers to Photo Detector Diode
ILED	Forward DC Current	-
V _{FLED}	Forward Voltage Drop	At I _{LED} = 50mA
VRLED	Reverse Voltage	-

10kV = 1V

 $^{2}V_{DR}$ = Detector diode voltage in reverse.



1µA = 1m V

Note: Specifications subject to change without notice. Photo is representation only.

VERSION: 3.0 EFFECTIVE: 27 DECEMBER 2021 PAGE: 3 OF 3